Silicon PNP Power Transistors 2SB1367

DESCRIPTION

- With TO-220F package
- Complement to type 2SD2059
- Low collector saturation voltage:
  $V_{CE(sat)}$=-2.0V(Max) at I_C=-4A,I_B=-0.4A
- Collector power dissipation:
  P_C=30W(T_C=25℃)

APPLICATIONS

- With general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

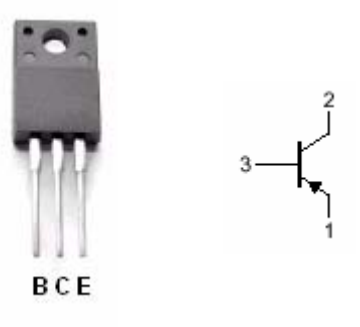


Fig.1 simplified outline (TO-220F) and symbol

固电半导体
INCHANGE SEMICONDUCTOR

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-5	A
I_B	Base current		-0.5	A
P_C	Collector dissipation	T_C=25℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-50mA ;I_B=0	-100			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-4A ;I_B=-0.4A			-2.0	V
V_{BE}	Base-emitter on voltage	I_C=-4A;V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-100V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-1.0	mA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-5V	40		240	
h_{FE-2}	DC current gain	I_C=-4A ; V_{CE}=-5V	20			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-5V		5.0		MHz
C_{OB}	Collector output capacitance	f=1MHz;V_{CB}=-10V		270		pF

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	70-140	120-240

固电半导体 INCHANGE SEMICONDUCTOR

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PACKAGE OUTLINE

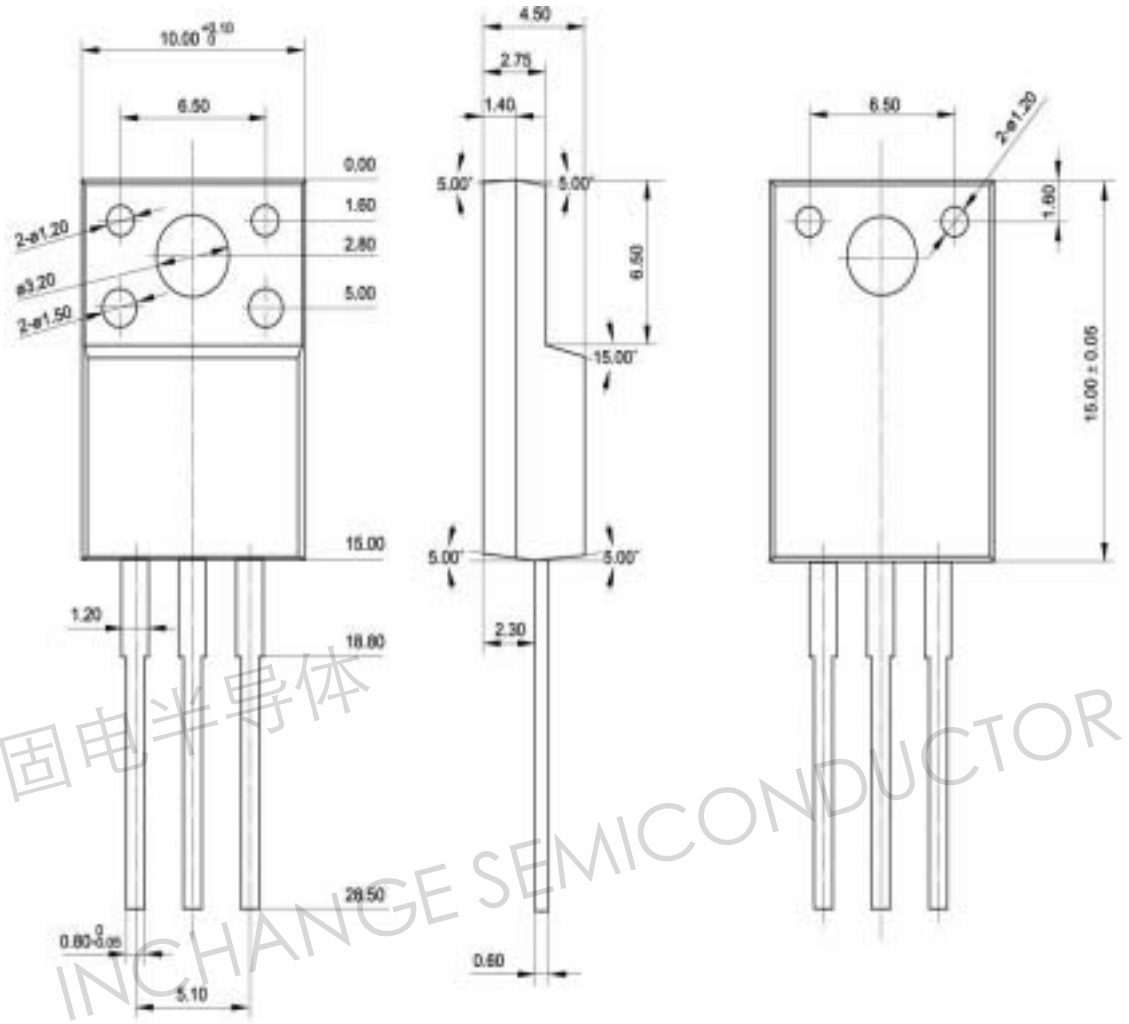


Fig.2 Outline dimensions

固电半导体
INCHANGE SEMICONDUCTOR

Silicon PNP Power Transistors 2SB1367

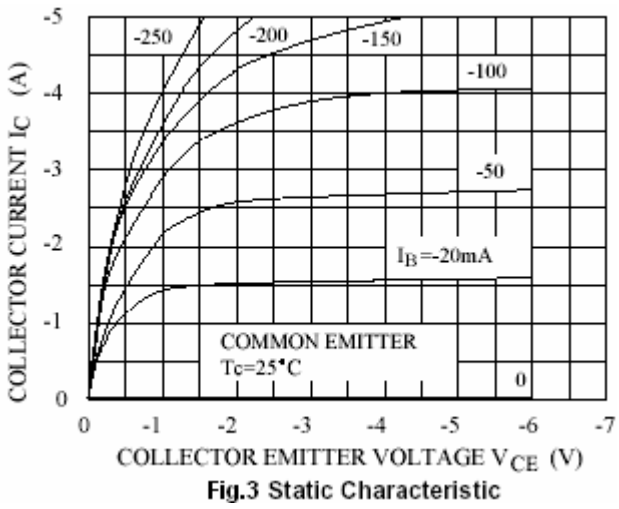


Fig.3 Static Characteristic

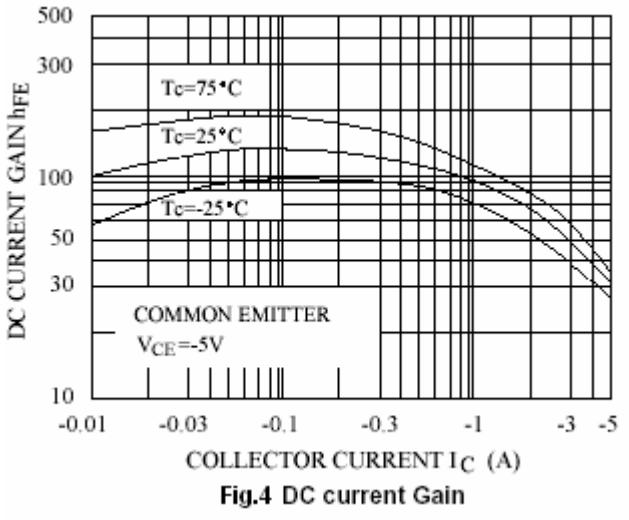


Fig.4 DC current Gain

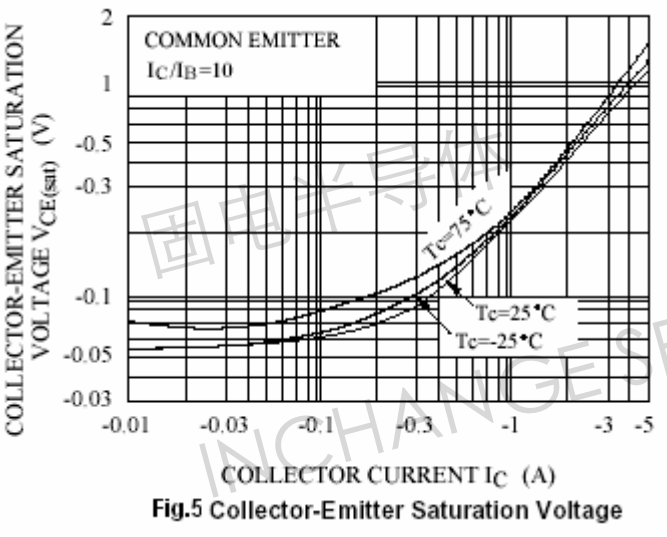


Fig.5 Collector-Emitter Saturation Voltage

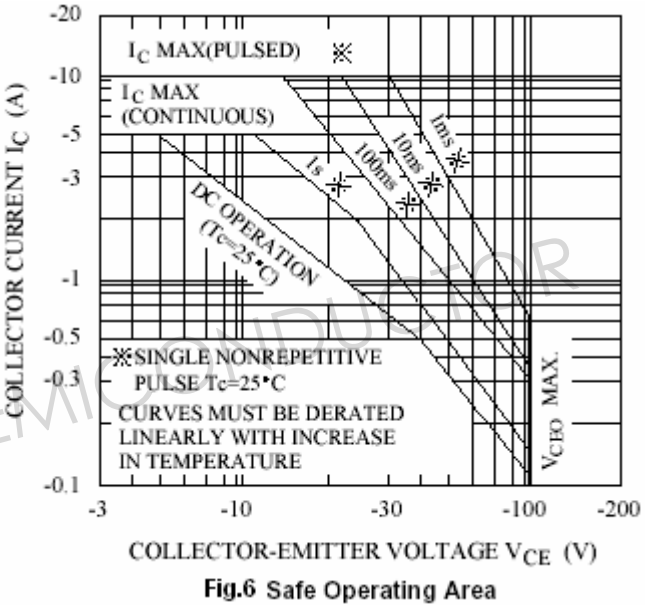


Fig.6 Safe Operating Area

INCHANGE SEMICONDUCTOR